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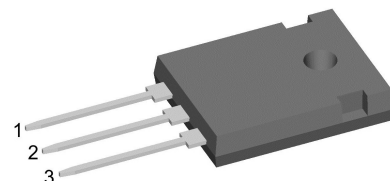
SiC Schottky Diode

$$V_{RRM} = 1200 \text{ V}$$

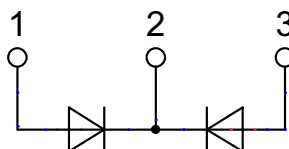
$$I_{FAV} = 2 \times 18 \text{ A}$$

Ultra fast switching
Zero reverse recovery
Common Cathode

Part number
DCG35C1200HR



Backside: isolated

 E72873


Features / Advantages:

- Ultra fast switching
- Zero reverse recovery
- Zero forward recovery
- Temperature independent switching behavior
- Positive temperature coefficient of forward voltage
- $T_{VJM} = 175^{\circ}\text{C}$

Applications:

- Solar inverter
- Uninterruptible power supply (UPS)
- Welding equipment
- Switched-mode power supplies
- Medical equipment
- High speed rectifier

Package: ISO247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms & Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

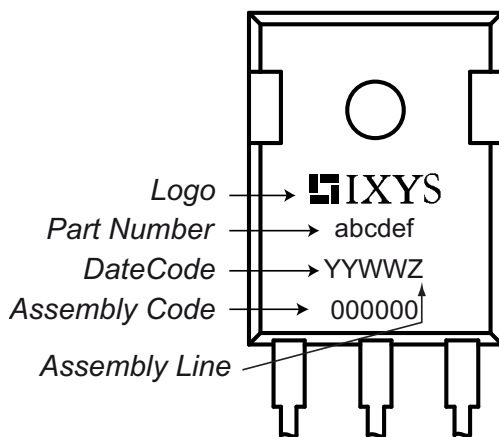
- to perform joint risk and quality assessments;
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

SiC Diode (per diode)				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V _{RSM}	max. non-repetitive reverse blocking voltage					1200	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 175°C		35 65	200 400	μA μA
V _F	forward voltage	I _F = 20 A I _F = 40 A	T _{VJ} = 25°C		1.5	1.8	V V
		I _F = 20 A I _F = 40 A	T _{VJ} = 175°C		2.2	3.0	V V
I _{FAV}	average forward current	T _C = 80°C T _C = 100°C		rectangular, d = 0.5 T _{VJ} = 175°C		18 16	A A
I _{F25}	forward current	based on typ. V _{F0} and r _F		T _C = 25°C		31.7	A
I _{F80}				T _C = 80°C		24.3	A
I _{F100}				T _C = 100°C		21.2	A
I _{FSM}	max forward surge current	t = 10 ms, half sine (50 Hz) t _p = 10 μs, pulse	T _{VJ} = 25°C V _R = 0V			1000	A A
V _{F0}	threshold voltage	for power loss calculation	T _{VJ} = 125°C 175°C		0.78 0.73		V V
r _F	slope resistance		T _{VJ} = 125°C 175°C		57.0 70.5		mΩ mΩ
Q _C	total capacitive charge		V _R = 800 V, I _F = 20A dI/dt = 200 A/μs	T _{VJ} = 25°C		99	
C	total capacitance	V _R = 0 V V _R = 400 V V _R = 800 V	T _{VJ} = 25°C, f = 1 MHz		1500 93 67		pF pF pF
R _{thJC} R _{thJH}	thermal resistance junction to case thermal resistance junction to heatsink	with heatsink compound; IXYS test setup			2.1	1.6	K/W K/W

Package ISO247				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I _{RMS}	RMS current	per terminal				70	A
T _{stg}	storage temperature			-40		150	°C
T _{op}	operation temperature			-40		150	°C
T _{VJ}	virtual junction temperature			-40		175	°C
Weight					6		g
M _D	mounting torque			0.8		1.2	Nm
F _C	mounting force with clip			40		120	N
d _{Spp/App}	creepage distance on surface /	terminal to terminal		2.7			mm
d _{Spb/Apb}	striking distance through air	terminal to backside		4.1			mm
V _{ISOL}	isolation voltage	t = 1 second t = 1 minute	50/60 Hz; RMS; I _{ISOL} < 1 mA		3600 3000		V V

Product Marking



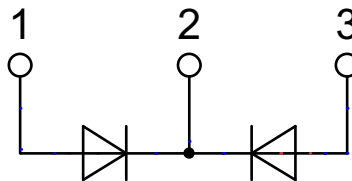
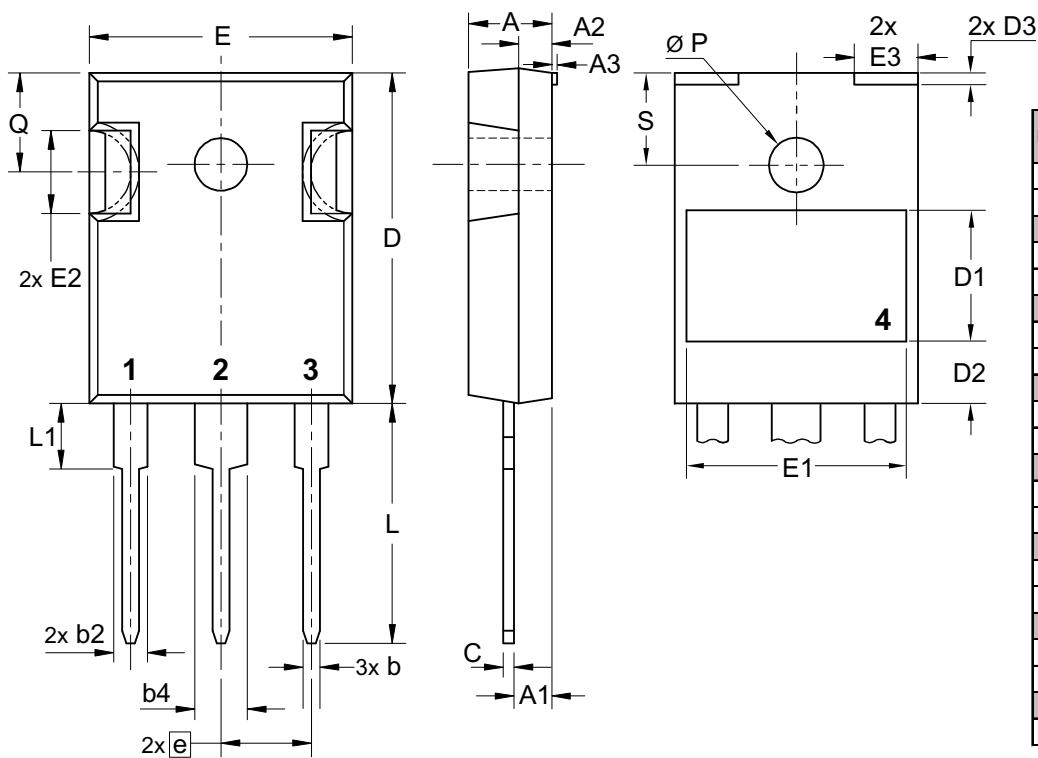
Part description

D = Diode
 C = SiC
 G = Extreme fast
 35 = Current Rating [A]
 C = Common Cathode
 1200 = Reverse Voltage [V]
 HR = ISO247 (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	DCG35C1200HR	DCG35C1200HR	Tube	30	521654

Equivalent Circuits for Simulation *on die level, typical

		$T_{VJ} = 125^{\circ}\text{C}$	$T_{VJ} = 175^{\circ}\text{C}$	
$V_{0\max}$	threshold voltage	0.78	0.73	V
$R_{0\max}$	slope resistance *	57.0	70.5	mΩ



Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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